

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	10/540410	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/10/27 15:37
L2	8	("20020153527" "5576556" "5786241" "6410373").PN.	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/10/27 15:38
L3	86	("20020153527" "5576556" "5786241" "6410373")	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/10/27 15:56
L4	9	("20010015441"   "20010025992"   "20010048107"   "20020001886"   "5403761"   "6228692"   "6259138"   "6303963"   "6331723").PN.	US-PGPU B; USPAT; USOCR	OR	OFF	2006/10/27 15:49
L5	9	("20010015441"   "20010025992"   "20010048107"   "20020001886"   "5403761"   "6228692"   "6259138"   "6303963"   "6331723").PN.	US-PGPU B; USPAT; USOCR	OR	OFF	2006/10/27 17:01
L6	173193	transistor with gate	US-PGPU B; USPAT; USOCR	OR	OFF	2006/10/27 17:01
L7	116939	transistor with gate same (source drain)	US-PGPU B; USPAT; USOCR	OR	OFF	2006/10/27 17:01

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L8	356	transistor with gate same (source drain) with (sidewall side adj wall wall near3 spacer) near5 (metal metallic conductive)	US-PGPU B; USPAT; USOCR	OR	ON	2006/10/27 17:19
L9	58	S8 and "LDD" same (source drain) with (sidewall side adj wall wall near3 spacer)	US-PGPU B; USPAT; USOCR	OR	ON	2006/10/27 17:19
L10	18	S9 and (source drain) with (silicide)	US-PGPU B; USPAT; USOCR	OR	ON	2006/10/27 17:14
L12	8028	gate same (metal metallic conductive polysilicon) near3 (sidewall side near3 wall wall near3 spacer spacer)	US-PGPU B; USPAT; USOCR	OR	ON	2006/10/27 17:22
L13	289	S12 and transistor with gate same (source drain) with (sidewall side adj wall wall near3 spacer) near5 (metal metallic conductive)	US-PGPU B; USPAT; USOCR	OR	ON	2006/10/27 17:23
L14	50	S13 and "LDD" same (source drain) with (sidewall side adj wall wall near3 spacer)	US-PGPU B; USPAT; USOCR	OR	ON	2006/10/27 17:23
L15	8028	gate same (metal metallic conductive polysilicon) near3 (sidewall side near3 wall wall near3 spacer spacer)	US-PGPU B; USPAT; USOCR	OR	ON	2006/10/27 17:21
L16	5995	gate same (metal metallic conductive polysilicon) near2 (sidewall side near3 wall wall near3 spacer spacer)	US-PGPU B; USPAT; USOCR	OR	ON	2006/10/27 17:22
L17	3619	gate same (metal metallic conductive polysilicon) near (sidewall side near3 wall wall near3 spacer spacer)	US-PGPU B; USPAT; USOCR	OR	ON	2006/10/27 17:22
L18	119	S17 and transistor with gate same (source drain) with (sidewall side adj wall wall near3 spacer) near5 (metal metallic conductive)	US-PGPU B; USPAT; USOCR	OR	ON	2006/10/27 17:23
L19	30	S18 and "LDD" same (source drain) with (sidewall side adj wall wall near3 spacer)	US-PGPU B; USPAT; USOCR	OR	ON	2006/10/27 17:23

### EAST Search History

L20	5	("5039621"   "5254490"   "5439846"   "5739066"   "6103590").PN.	US-PGPU B; USPAT; USOCR	OR	OFF	2006/10/27 17:39
L21	6	("4521448"   "4727038"   "4804636"   "4868617"   "4925807"   "4971922").PN.	US-PGPU B; USPAT; USOCR	OR	OFF	2006/10/27 17:46
L22	13	("4488351"   "4587718"   "4613882"   "4616401"   "4658496"   "4680603"   "4703551"   "4727038"   "4735680"   "4753898"   "4788160"   "4824796"   "4835112").PN.	US-PGPU B; USPAT; USOCR	OR	OFF	2006/10/27 17:50
L23	4	("4363696"   "4597824"   "4654680"   "4746219").PN.	US-PGPU B; USPAT; USOCR	OR	OFF	2006/10/27 18:03
L24	12	("4510670"   "4526665"   "4528744"   "4541166"   "4558507"   "4563805"   "4575920"   "4585517"   "4587710"   "4593454"   "4613882"   "4622735").PN.	US-PGPU B; USPAT; USOCR	OR	OFF	2006/10/27 18:15
L25	35	"4925807"	US-PGPU B; USPAT; USOCR	OR	OFF	2006/10/27 18:15